NXP USA Inc. - MKL17Z32VDA4R Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, FlexIO, SPI, UART/USART
Peripherals	DMA, I²S, PWM, WDT
Number of I/O	32
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 15x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	36-XFBGA
Supplier Device Package	36-XFBGA (3.5x3.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl17z32vda4r

- Configurable for short and long timeout values, the longest timeout is up to 262 seconds
- Support window mode

2.2 Peripheral features

The following sections describe the features of each peripherals of the chip.

2.2.1 BME

The Bit Manipulation Engine (BME) provides hardware support for atomic read-modify-write memory operations to the peripheral address space in Cortex-M0+ based microcontrollers. It reduces up to 30% of the code size and up to 9% of the cycles for bit-oriented operations to peripheral registers.

The BME supports unsigned bit field extract, load-and-set 1-bit, load-and-clear 1-bit, bit field insert, logical AND/OR/XOR operations with byte, halfword or word-sized data type.

2.2.2 DMA and DMAMUX

The DMA controller module enables fast transfers of data, which provides an efficient way to move blocks of data with minimal processor interaction. The DMA controller in this device implements four channels which can be routed from up to 63 DMA request sources through DMA MUX module. Some of the peripheral request sources have asynchronous DMA capability which can be used to wake MCU from Stop mode. The peripherals which have such capability include LPUART0, LPUART1, FlexIO, TPM0-TPM2, ADC0, CMP0, PORTA-PORTE. The DMA channel 0 and 1 can be periodically triggered by PIT via DMA MUX.

Main features are listed below:

- Dual-address transfers via 32-bit master connection to the system bus and data transfers in 8-, 16-, or 32-bit blocks
- Supports programmable source and destination address and transfer size, optional modulo addressing from 16 bytes to 256 KB
- Automatic updates of source and destination addresses

- Full-duplex or single-wire bidirectional mode
- Programmable transmit bit rate
- Double-buffered transmit and receive data register
- Serial clock phase and polarity options
- Slave select output
- Mode fault error flag with CPU interrupt capability
- Control of SPI operation during wait mode
- Selectable MSB-first or LSB-first shifting
- Programmable 8- or 16-bit data transmission length
- Receive data buffer hardware match feature
- 64-bit FIFO mode for high speed/large amounts of data transfers
- Support DMA

2.2.14 I2C

This device contains two I2C modules, which support up to 1 Mbits/s by dual buffer features, and address match to wake MCU from the low power mode.

I2C modules support DMA transfer, and the interrupt condition can trigger DMA request when DMA function is enabled.

The I2C modules have the following features:

- Support for system management bus (SMBus) Specification, version 2
- Software programmable for one of 64 different serial clock frequencies
- Software-selectable acknowledge bit
- Arbitration-lost interrupt with automatic mode switching from master to slave
- Calling address identification interrupt
- START and STOP signal generation and detection
- Repeated START signal generation and detection
- Acknowledge bit generation and detection
- Bus busy detection
- General call recognition
- 10-bit address extension
- Programmable input glitch filter
- Low power mode wakeup on slave address match
- Range slave address support
- DMA support
- Double buffering support to achieve higher baud rate

Table 17. TPM1 signal descriptions

Chip signal name	Module signal name	Description	I/O
TPM_CLKIN[1:0]	TPM_EXTCLK	External clock. TPM external clock can be selected to increment the TPM counter on every rising edge synchronized to the counter clock.	I
TPM1_CH[1:0]	TPM_CHn	TPM channel (n = 1 to 0). A TPM channel pin is configured as output when configured in an output compare or PWM mode and the TPM counter is enabled, otherwise the TPM channel pin is an input.	I/O

Table 18. TPM2 signal descriptions

Chip signal name	Module signal name	Description	I/O
TPM_CLKIN[1:0]	TPM_EXTCLK	External clock. TPM external clock can be selected to increment the TPM counter on every rising edge synchronized to the counter clock.	I
TPM2_CH[1:0]	TPM_CHn	TPM channel (n = 1 to 0). A TPM channel pin is configured as output when configured in an output compare or PWM mode and the TPM counter is enabled, otherwise the TPM channel pin is an input.	I/O

Table 19. LPTMR0 signal descriptions

Chip signal name	Module signal name	Description	I/O
LPTMR0_ALT[3:1]	LPTMR0_ALT*n*	Pulse Counter Input pin	I

Table 20. RTC signal descriptions

Chip signal name	Module signal name	Description	I/O
RTC_CLKOUT[1]	RTC_CLKOUT	1 Hz square-wave output or OSCERCLK	O

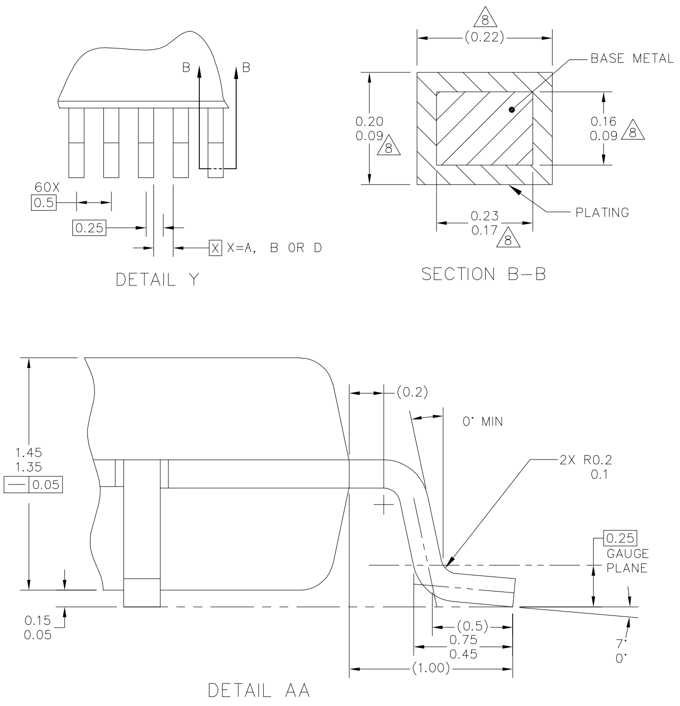
1. RTC_CLKOUT can also be driven with OSCERCLK via SIM control bit SIM_SOPT[RCTCLKOUTSEL]

4.3.6 Communication interfaces

Table 21. SPI0 signal descriptions

Chip signal name	Module signal name	Description	I/O
SPI0_MISO	MISO	Master Data In, Slave Data Out	I/O

Table continues on the next page...



NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.

2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.

△3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.

△4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.

△5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 MM AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 MM.

△6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 MM PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.

△7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.

△8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 MM AND 0.25 MM FROM THE LEAD TIP.

Figure 12. 64-pin LQFP package dimensions 2

Table 33. Voltage and current absolute operating ratings (continued)

Symbol	Description	Min.	Max.	Unit
V_{IO}	IO pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

5.2 General

5.2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

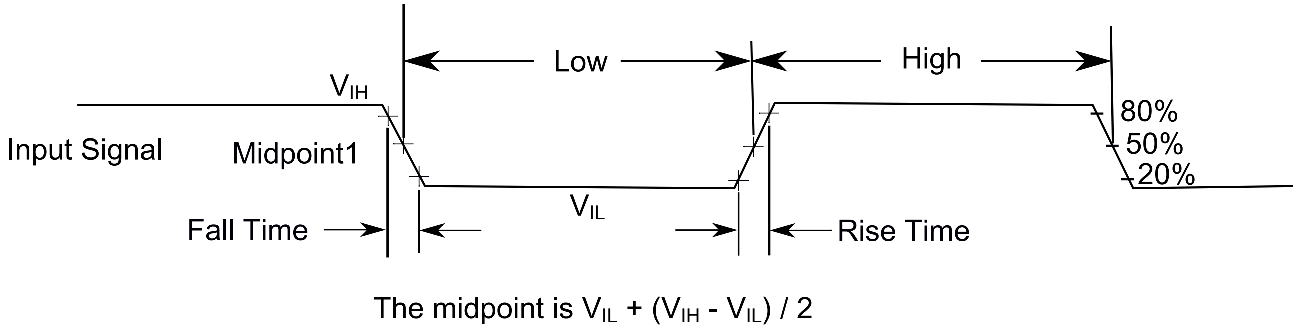


Figure 19. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume that the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength

5.2.2 Nonswitching electrical specifications

Table 39. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
		40	40	40	40	40	40	
I_{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx or VLLSx mode.	45	45	45	45	45	45	µA
I_{ADC}	ADC peripheral adder combining the measured values at V_{DD} and V_{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	320	320	320	320	320	320	µA

5.2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG-Lite in HIRC for run mode, and LIRC for VLPR mode
- No GPIOs toggled
- Code execution from flash
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

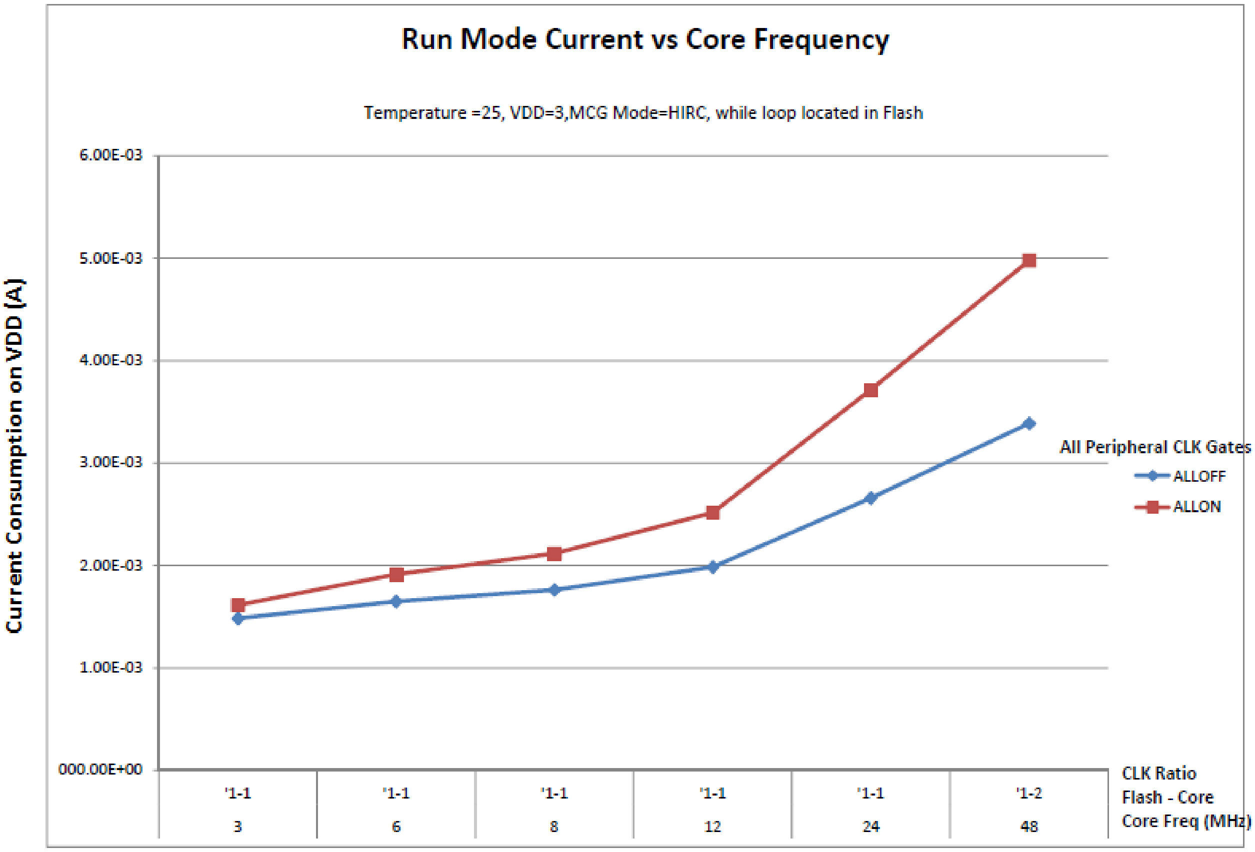


Figure 20. Run mode supply current vs. core frequency

5.2.3.2 General switching specifications

These general-purpose specifications apply to all signals configured for GPIO and UART signals.

Table 42. General switching specifications

Description	Min.	Max.	Unit	Notes
GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
Port rise and fall time	—	36	ns	3

1. The synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. 75 pF load

5.2.4 Thermal specifications

5.2.4.1 Thermal operating requirements

Table 43. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	125	°C	
T_A	Ambient temperature	–40	105	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

5.2.4.2 Thermal attributes

NOTE

The 48 QFN and 64 MAPBGA packages for this product are not yet available. However, it is included in Package Your Way program for Kinetis MCUs. Visit freescale.com/KPYW for more details.

Table 44. Thermal attributes

Board type	Symbol	Description	32 QFN	36 XFBGA	64 LQFP	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	101	81.5	71	°C/W	1, 2, 3
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	33	54.7	53	°C/W	1, 2, 3,4
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	84	71.3	60	°C/W	1, 4, 5
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	28	50.0	47	°C/W	1, 4, 5
—	$R_{\theta JB}$	Thermal resistance, junction to board	13	58.0	35	°C/W	6
—	$R_{\theta JC}$	Thermal resistance, junction to case	1.7	45.3	21	°C/W	7
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	3	1.2	5	°C/W	8
—	Ψ_{JB}	Thermal characterization parameter, junction to package bottom (natural convection)	-	44.5	-	°C/W	9

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
3. Per JEDEC JESD51-2 with natural convection for horizontally oriented board. Board meets JESD51-9 specification for 1s or 2s2p board, respectively.
4. Per JEDEC JESD51-6 with the board horizontal.
5. Per JEDEC JESD51-6 with forced convection for horizontally oriented board. Board meets JESD51-9 specification for 1s or 2s2p board, respectively.
6. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
7. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
8. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.
9. Thermal characterization parameter indicating the temperature difference between package bottom center and the junction temperature per JEDEC JESD51-12. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.

5.3 Peripheral operating requirements and behaviors

5.3.1 Core modules

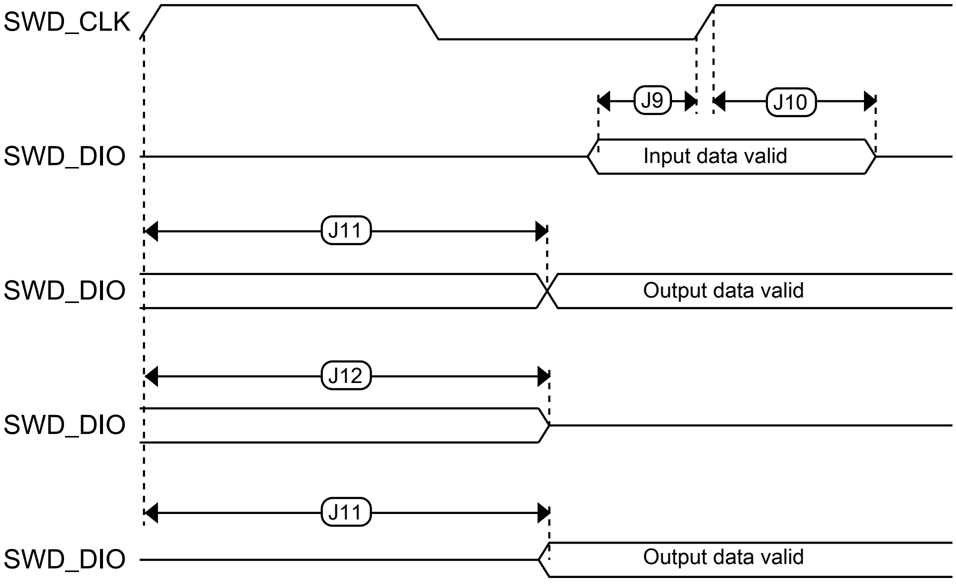


Figure 23. Serial wire data timing

5.3.2 System modules

There are no specifications necessary for the device's system modules.

5.3.3 Clock modules

5.3.3.1 MCG-Lite specifications

Table 46. IRC48M specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD48M}	Supply current	—	400	500	µA	
f_{irc48m}	Internal reference frequency	—	48	—	MHz	
$\Delta f_{irc48m\_ol\_lv}$	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over temperature	—	± 0.5	± 1.5	$\%f_{irc48m}$	
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over temperature	—	± 0.5	± 1.0	$\%f_{irc48m}$	1
J_{cyc_irc48m}	Period Jitter (RMS)	—	35	150	ps	
$t_{irc48mst}$	Startup time	—	2	3	µs	2

1. The maximum value represents characterized results equivalent to the mean plus or minus three times the standard deviation (mean±3 sigma).
2. IRC48M startup time is defined as the time between clock enablement and clock availability for system use. Enable the clock by one of the following settings:
    - MCG operating in an external clocking mode and MCG_C7[OSCSEL]=10, or
    - SIM_SOPT2[PLLFLLSEL]=11

Table 47. IRC8M/2M specification

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_2M}	Supply current in 2 MHz mode	—	14	17	µA	—
I_{DD_8M}	Supply current in 8 MHz mode	—	30	35	µA	—
f_{IRC_2M}	Output frequency	—	2	—	MHz	—
f_{IRC_8M}	Output frequency	—	8	—	MHz	—
$f_{IRC\_T\_2M}$	Output frequency range (trimmed)	—	—	±3	$\%f_{IRC}$	—
$f_{IRC\_T\_8M}$	Output frequency range (trimmed)	—	—	±3	$\%f_{IRC}$	—
T_{su_2M}	Startup time	—	—	12.5	µs	—
T_{su_8M}	Startup time	—	—	12.5	µs	—

5.3.3.2 Oscillator electrical specifications

5.3.3.2.1 Oscillator DC electrical specifications

Table 48. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	µA	
	• 8 MHz (RANGE=01)	—	300	—	µA	
	• 16 MHz	—	950	—	µA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	µA	
	• 4 MHz	—	400	—	µA	
	• 8 MHz (RANGE=01)	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	

Table continues on the next page...

Table 48. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

5.3.3.2.2 Oscillator frequency specifications

Table 49. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL
2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

5.3.4 Memories and memory interfaces

5.3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

5.3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 50. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	—
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

5.3.4.1.2 Flash timing specifications — commands

Table 51. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	—
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	0.9	ms	1
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	—
t_{ersall}	Erase All Blocks execution time	—	70	575	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{ersallu}$	Erase All Blocks Unsecure execution time	—	70	575	ms	2

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

5.3.4.1.3 Flash high voltage current behaviors

Table 52. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

5.3.4.1.4 Reliability specifications

Table 53. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
			Program Flash			

Table continues on the next page...

Table 54. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	ksps	5
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

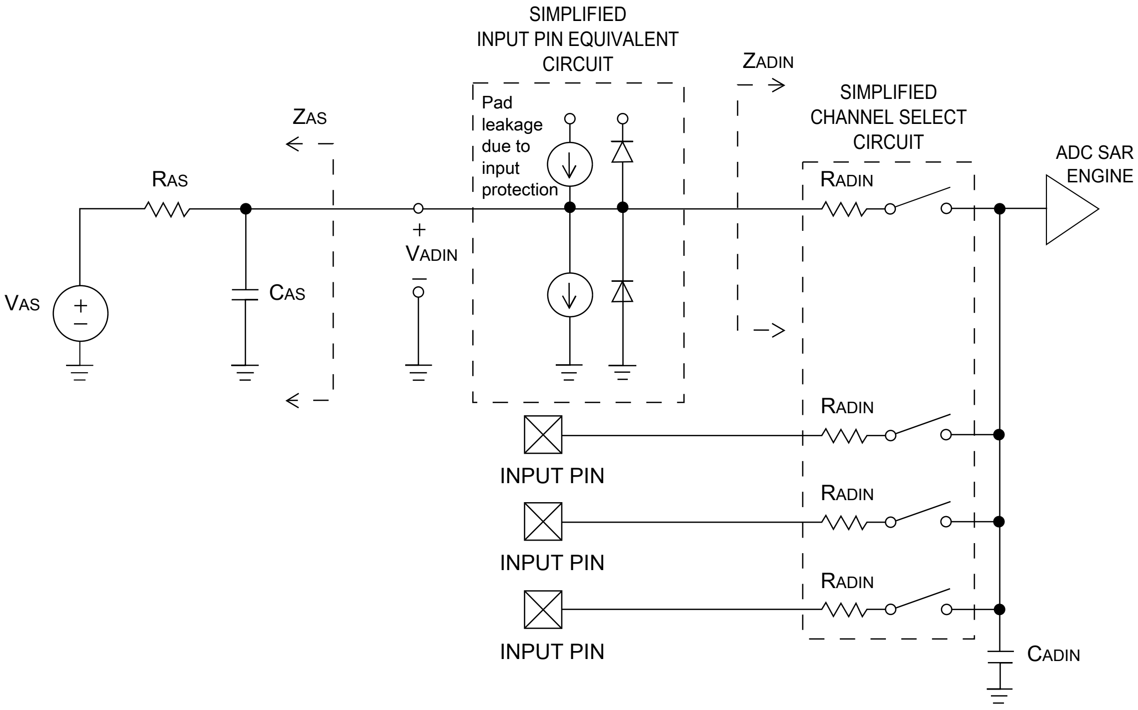


Figure 24. ADC input impedance equivalency diagram

Table 55. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
		• Avg = 32					
SFDR	Spurious free dynamic range	16-bit differential mode • Avg = 32	82	95	—	dB	7
		16-bit single-ended mode • Avg = 32	78	90	—	dB	
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

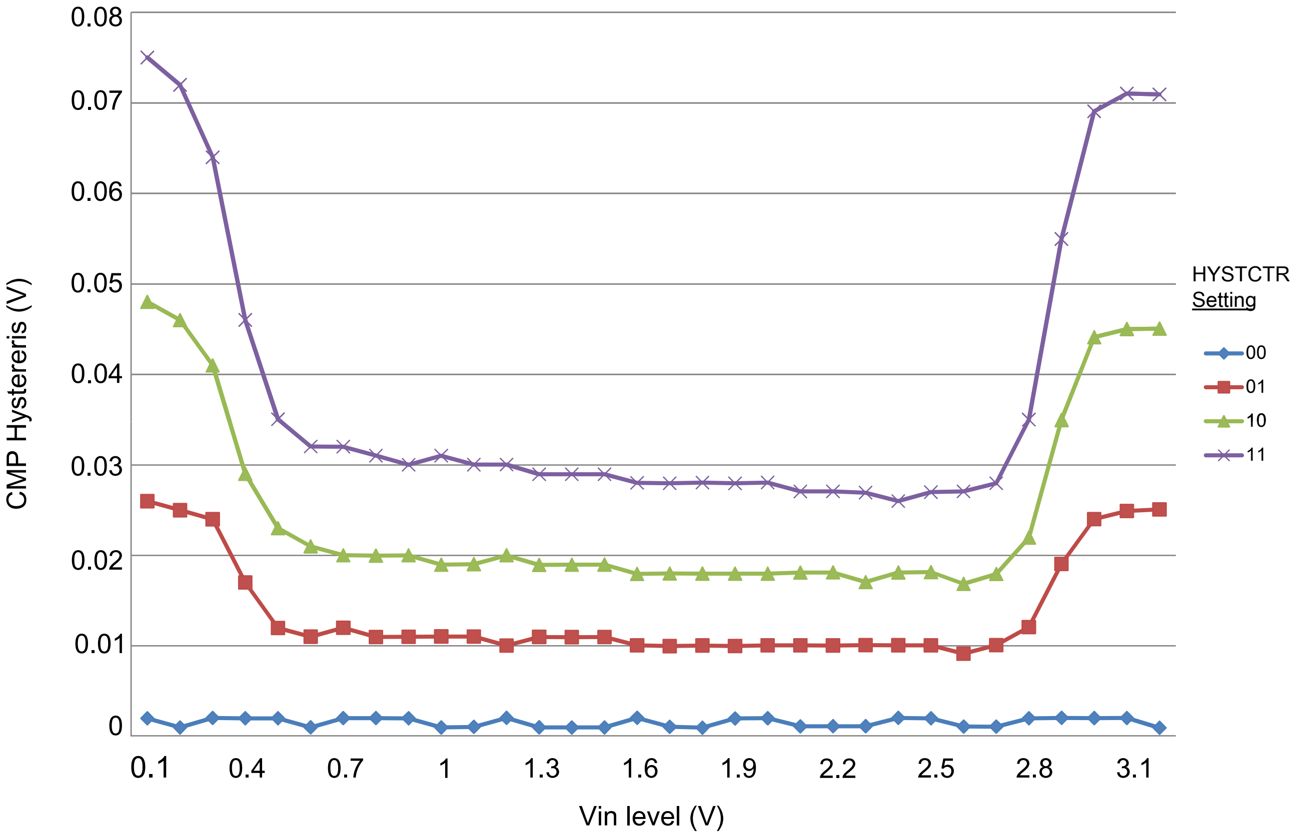


Figure 27. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Table 60. SPI master mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	f_{periph}/2048	f_{periph}/2	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	18	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	15	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. t_{periph} = 1/f_{periph}

Table 61. SPI master mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	f_{periph}/2048	f_{periph}/2	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	52	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. t_{periph} = 1/f_{periph}

6.1.4 Digital design

Ensure that all I/O pins cannot get pulled above VDD (Max I/O is VDD+0.3V).

CAUTION

> Do not provide power to I/O pins prior to VDD, especially the RESET_b pin.

- RESET_b pin

  The RESET_b pin is an open-drain I/O pin that has an internal pullup resistor. An external RC circuit is recommended to filter noise as shown in the following figure. The resistor value must be in the range of 4.7 kΩ to 10 kΩ; the recommended capacitance value is 0.1 µF. The RESET_b pin also has a selectable digital filter to reject spurious noise.

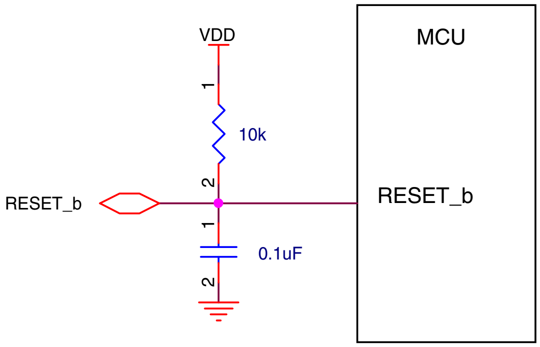


Figure 36. Reset circuit

When an external supervisor chip is connected to the RESET_b pin, a series resistor must be used to avoid damaging the supervisor chip or the RESET_b pin, as shown in the following figure. The series resistor value (RS below) must be in the range of 100 Ω to 1 kΩ depending on the external reset chip drive strength. The supervisor chip must have an active high, open-drain output.

For all other partner-developed software and tools, visit http://www.freescale.com/partners.

7 Part identification

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Table 67. Part number fields description

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
KL##	Kinetis family	• KL17
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB
R	Silicon revision	• (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm)[1] • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm)[1] • DA = 36 XFBGA (3.5 mm x 3.5 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz

Table continues on the next page...